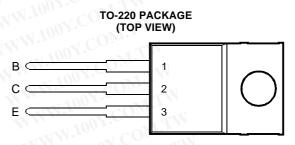
- Designed for Complementary Use with TIP130, TIP131 and TIP132
- 70 W at 25°C Case Temperature
- 8 A Continuous Collector Current
- Minimum h_{FE} of 1000 at 4 V, 4 A



Pin 2 is in electrical contact with the mounting base.

MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT	
MANN COMMENT	TIP135	TOON CO	-60		
Collector-base voltage (I _E = 0)	TIP136	V _{CBO}	-80	V	
	TIP137	W.1001.	-100		
M. W. COM THE WAY ON COME	TIP135	100X.C	-60		
Collector-emitter voltage (I _B = 0)	TIP136	V _{CEO}	-80	V	
	TIP137	11 100 1.	-100		
Emitter-base voltage		V _{EBO}	-5	V	
Continuous collector current	-XX	Ic	CO -8	Α	
Peak collector current (see Note 1)	(1,1,1)	I _{CM}	-12	Α	
Continuous base current	WTI	I _B	-0.3	Α	
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)			70	W	
Continuous device dissipation at (or below) 25°C free air temperature (see N	Note 3)	P _{tot}	2	W	
Unclamped inductive load energy (see Note 4)	WTI	½LI _C ²	75	mJ	
Operating junction temperature range	ON	Ti	-65 to +150	°C	
Storage temperature range	COMIT	T _{stg}	-65 to +150	°C	
Lead temperature 3.2 mm from case for 10 seconds		TL	260	°C	

NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%.$

- 2. Derate linearly to 150°C case temperature at the rate of 0.56 W/°C.
- 3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.
- 4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)}$ = -5 mA, R_{BE} = 100 Ω , $V_{BE(off)}$ = 0, R_S = 0.1 Ω , V_{CC} = -20 V.

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TIP135, TIP136, TIP137 PNP SILICON POWER DARLINGTONS

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electrical characteristics at 25°C case temperature

	PARAMETER	COM	TEST	CONDITIONS		MIN	TYP	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = -30 mA	I _B = 0	(see Note 5)	TIP135 TIP136	-60 -80			V
Ulli	Significant voltage	. OUT CO	TW	MW.	TIP137	-100			
	Collector-emitter	$V_{CE} = -30 \text{ V}$	$I_B = 0$		TIP135	-CVV		-0.5	
I _{CEO}	cut-off current	$V_{CE} = -40 \text{ V}$	$I_B = 0$		TIP136	1.7		-0.5	mA
COM Cut-0	cut on current	$V_{CE} = -50 \text{ V}$	$I_B = 0$		TIP137	WTIL		-0.5	
- c01	Collector cut-off current	$V_{CB} = -60 \text{ V}$	$I_E = 0$	I TINV	TIP135	Diam.	X	-0.2	
		$V_{CB} = -80 \text{ V}$	$I_E = 0$		TIP136	WI.I.		-0.2	
of CO		$V_{CB} = -100 \text{ V}$	$I_{E} = 0$		TIP137	7 7	W	-0.2	mA
I _{CBO}		$V_{CB} = -60 \text{ V}$	$I_{E} = 0$	$T_{C} = 100^{\circ}C$	TIP135	\mathbf{C}_{OMr} .	-XX	-1	
		$V_{CB} = -80 \text{ V}$	$I_E = 0$	T _C = 100°C	TIP136	Mos	7.4.	-1	
		$V_{CB} = -100 \text{ V}$	$I_{E} = 0$	$T_{\rm C} = 100^{\circ}{\rm C}$	TIP137	1.00	WT	-1	
I _{EBO}	Emitter cut-off current	V _{EB} = -5 V	I _C = 0	V.TW V	WW.100	V.CO	M.TV	-5	mA
h 00	Forward current	V _{CE} = -4 V	I _C = -1 A	(see Notes 5 and 6)	6)	500	Tim	7	
h _{FE}	transfer ratio	V _{CE} = -4 V	$I_C = -4 A$		0)	1000	Diar.	15000	
V-110	Collector-emitter	$I_B = -16 \text{ mA}$	$I_C = -4 A$	(and Notes E and	6)	Ing.	·OM·	-2	V
V _{CE(sat)}	saturation voltage	$I_B = -30 \text{ mA}$	$I_C = -6 A$	(see Notes 5 and 6)	0)	1007.		-3	V
V_{BE}	Base-emitter voltage	V _{CE} = -4 V	I _C = -4 A	(see Notes 5 and	6)	N.100Y	COL	-2.5	V
C _{obo}	Output capacitance	V _{CB} = -10 V	$I_E = 0$	TIN	MAG	100	1.0	200	pF
V _{EC}	Parallel diode forward voltage	I _E = -8 A	I _B = 0	(see Notes 5 and	6)	M.10	17.C	-3.5	V

NOTES: 5. These parameters must be measured using pulse techniques, $t_D = 300 \mu s$, duty cycle $\leq 2\%$.

thermal characteristics

PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance	MW	10.2	1.78	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance	- 11	Mir	62.5	°C/W
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^{6.} These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN

VS **COLLECTOR CURRENT** TCS135AA $T_c = -40^{\circ}C$ $T_c = 25^{\circ}C$ $T_c = 100$ °C 10000 Current 2 Typical 1000 h. -4 V = 300 µs, duty cycle < 2% 100 -0-5 -1-0 I_c - Collector Current - A

Figure 1.

COLLECTOR-EMITTER SATURATION VOLTAGE

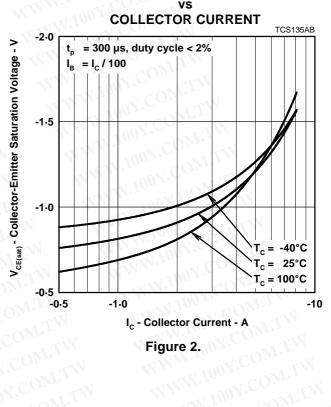
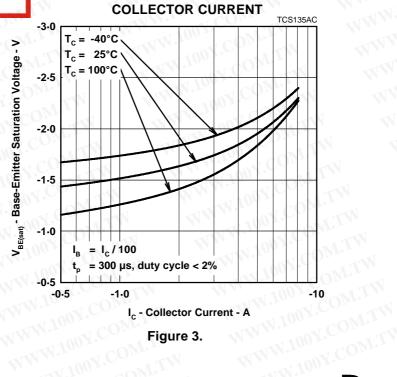


Figure 2. WWW.100Y.COM.TW

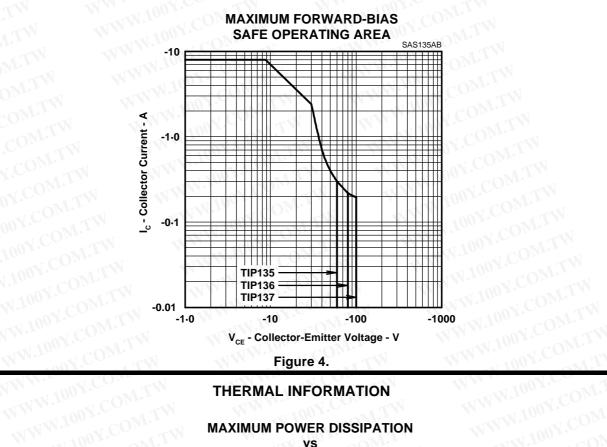
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BASE-EMITTER SATURATION VOLTAGE



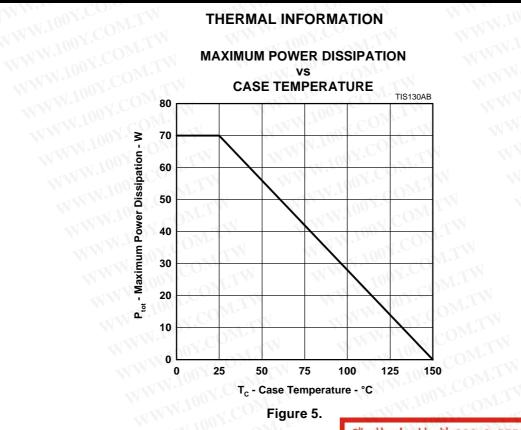
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THERMAL INFORMATION

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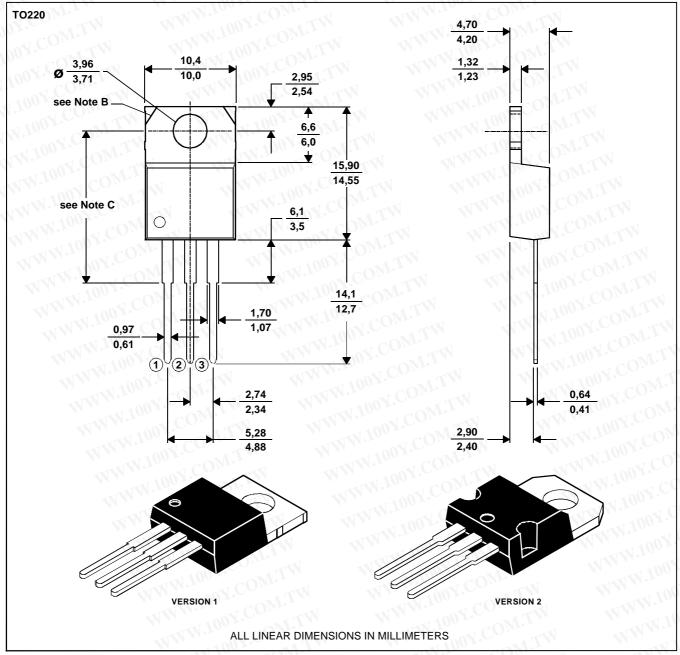
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MECHANICAL DATA

TO-220

3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



NOTES: A. The centre pin is in electrical contact with the mounting tab.

- B. Mounting tab corner profile according to package version.
- C. Typical fixing hole centre stand off height according to package version. Version 1, 18.0 mm. Version 2, 17.6 mm.

MDXXBE

PRODUCT INFORMATION

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